

Study of Contamination and Key Parameters in Wafer Vertical Probe Card Testing



Cedric Hermet – STMicroelectronics France Salvatore De Siena – Technoprobe Italy

Stéphanie Escoubas & Luc Favre – IM2NP Laboratory, AMU

Outline

- Introduction
- Goals
- Experimental setup
- Influence of current
- Influence of force
- Influence of initial tip surface conditions
- Conclusions
- Follow-On work
- References & Acknowledgements

Introduction

- Contamination is well known to cause failures in the world of semiconductor testing. Nevertheless, the nature, source and influence of this contamination is not always clearly identified.
- These contaminations are particles or films whose micrometric size makes them difficult to detect and inspect. They are generally found on tips surface, causing testing issues. But we sometimes forget that these contaminants are mobile in a test cell and can also affect the device under test.



Goals

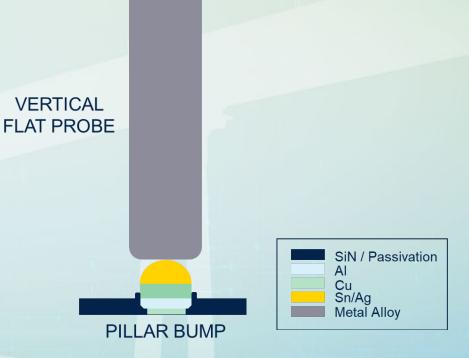
- 1. Seeking for key parameters playing a role in contamination and electrical performance (contact resistance CRES).
- 2. Understanding the various contamination phenomenon and their impact.

Long Term Goal

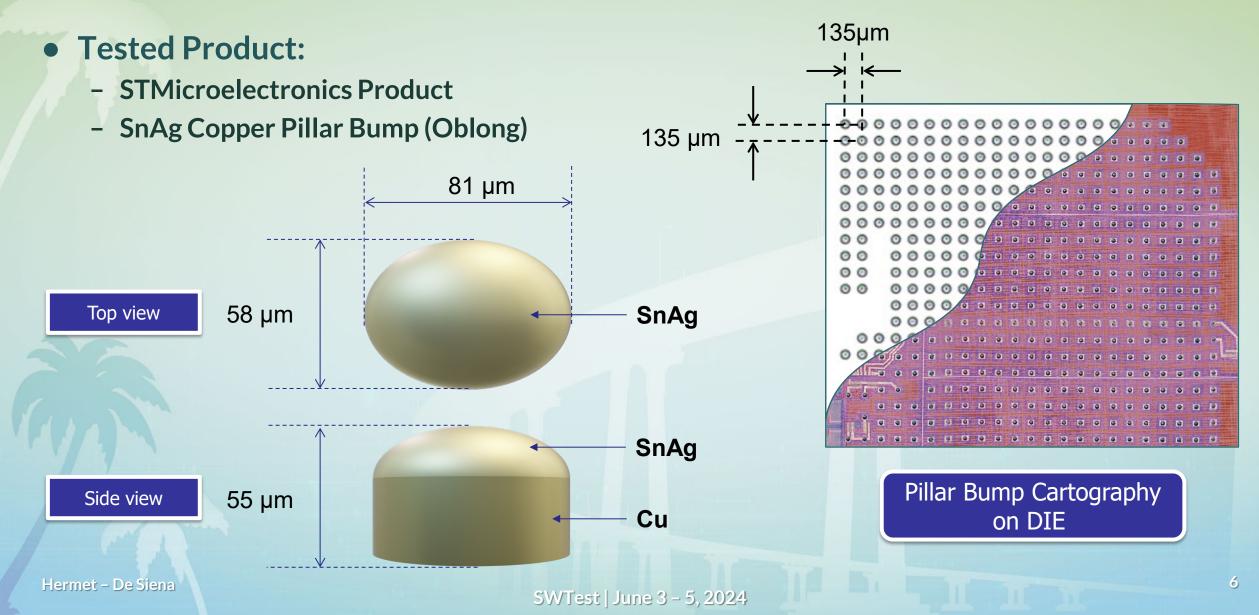
Developing innovative probe cards, improve their use and think new cleaning protocols.

Studied Parameters

- Experimental trials have been conducted on the following parameters in order to evaluate their influence on contamination and test performance:
 - Current intensity
 - Spacing from 0.25mA to 250mA
 - Force induced by probe length
 - Impact of free length vs free tip length
 - Initial tip surface conditions
 - Rough vs mirror-like tip surface

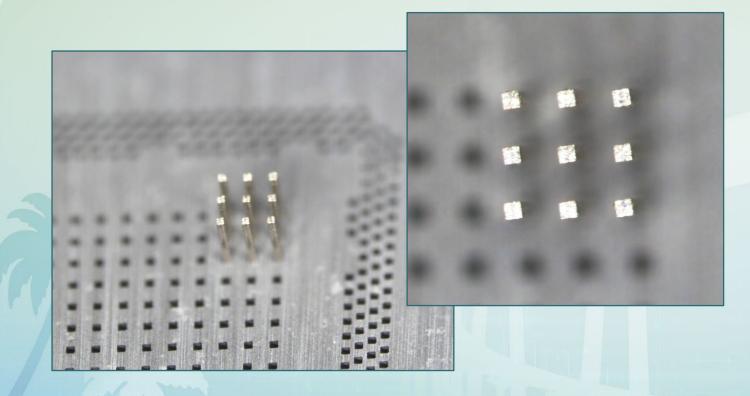


Experimental Setup



Experimental Setup

• Vertical Probe Card test vehicle: - TPEG S90 SA2 XLT Flat Technology

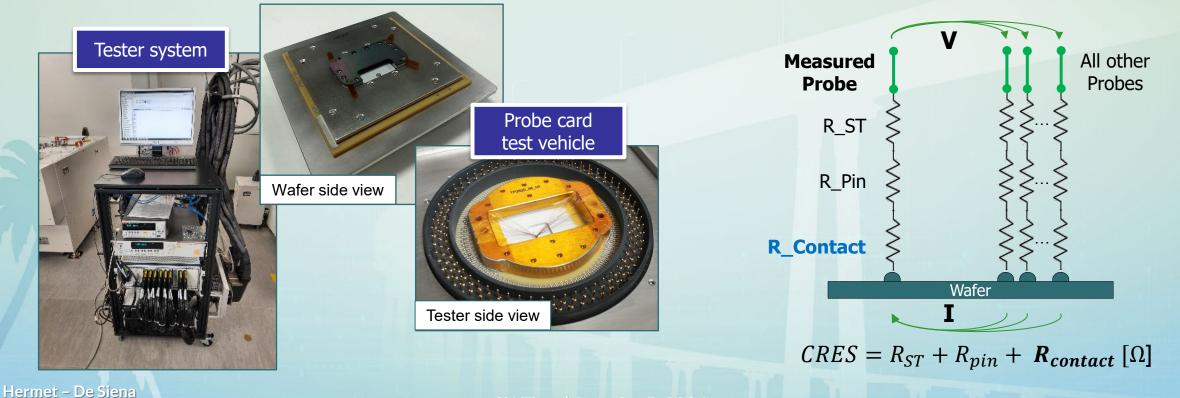


Technology name	TPEG™ S90 SA2 FLAT XLT	
Needle Length	4700 µm	
Tip finishing	Flat	
XLT	Yes	
Force (at 75um OT)	2.5 g	
Pin Current (CCC)	1450 mA	
Probe dimension	55x55 µm²	
Min pitch: Linear	90 µm	
Min pitch: FA regular	90 µm	
Min pitch: FA any angle	110 µm	
Temperature range	-45 to +175°C	
Probe alloy	SA2	
Probe resistance	58 mOhm	
Max working OD	100 µm	

Experimental Setup

- Test Cell and Functioning Mode:
 - Accretech UF3000 Prober
 - Specific Setup: STMicroelectronics Probing Parameters
 - Keithley Multimeter: CRES Measurement with forced current

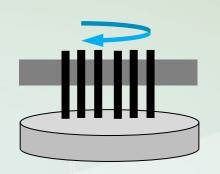


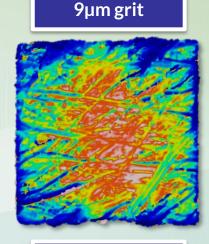


Experimental setup

Lapping Process:

Probe finishing	Cleaning media	Abrasive Size	Abrasive Type
FLAT	3M blue paper 266X	9µm	AIO ₂
FLAT	3M pink paper 266X	3µm	AIO ₂
FLAT	3M green paper 265X	1µm	AIO ₂





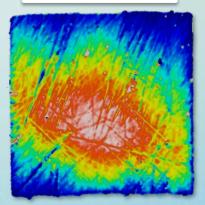
• Inspection Tools & Software:

- Morphological inspection
- Contamination identification
- Chemical semi-quantification
- Contact surface measurement
- Surface roughness measurement
- Contamination volume estimation _

SEM-EDX Microscope

Confocal Microscope + Gwyddion

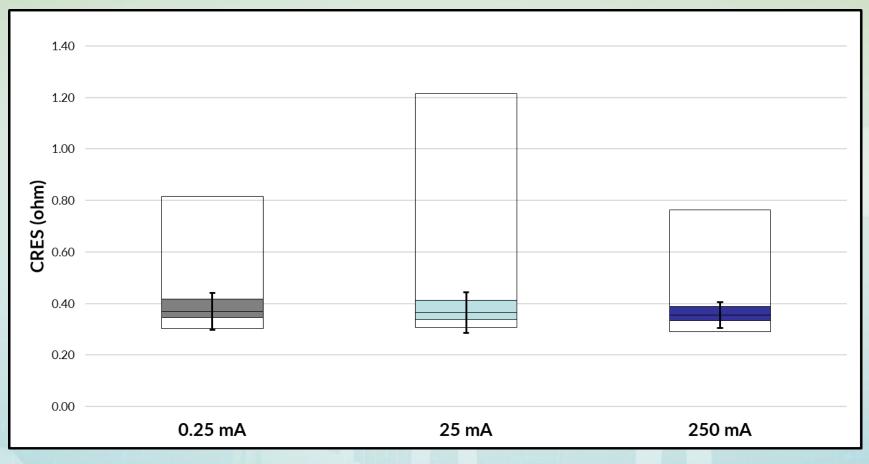




Hermet – De Siena

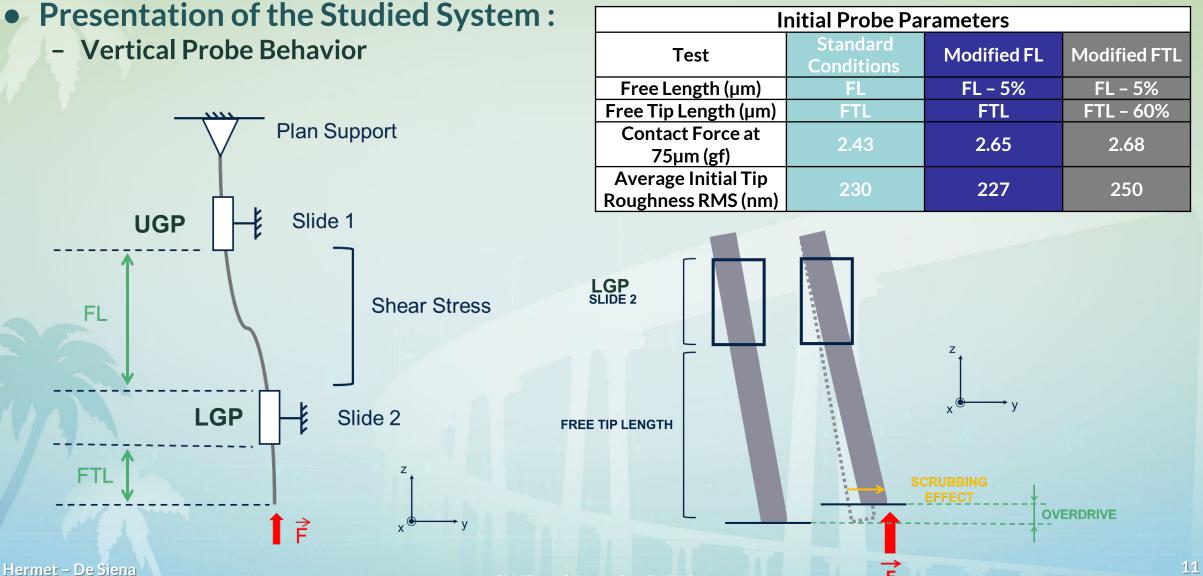
Influence of Current

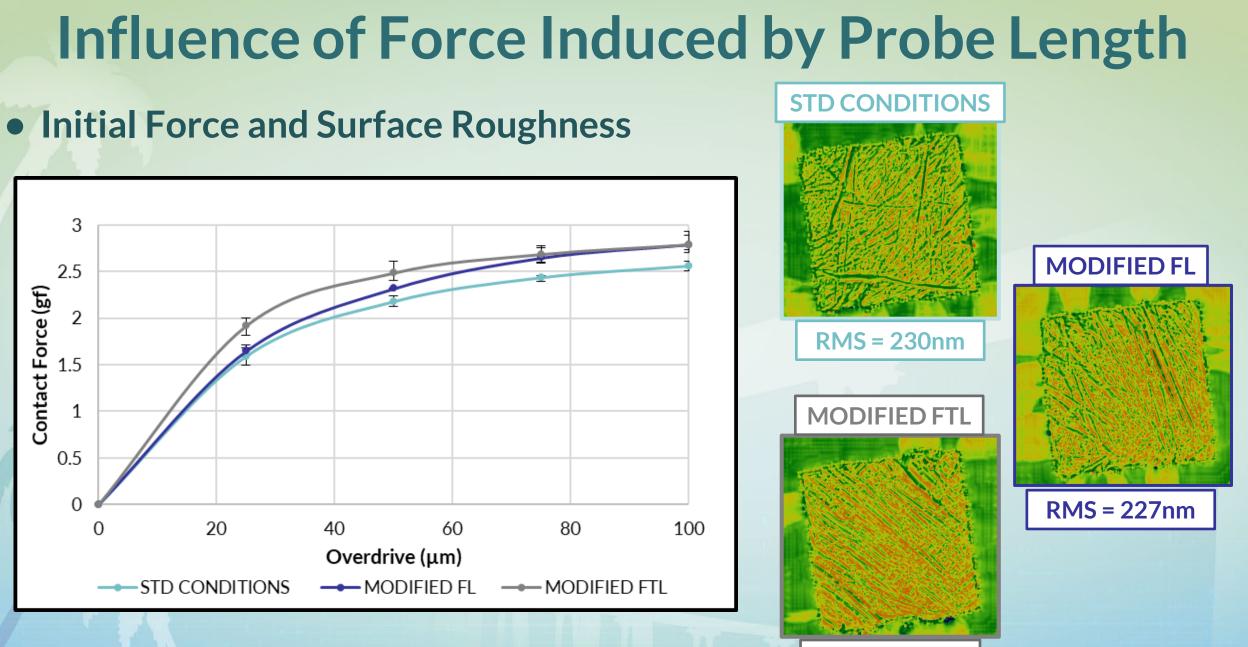
• Single Current Test over 1000 Touchdowns



No difference observed in terms of tip surface contamination

Influence of Force Induced by Probe Length





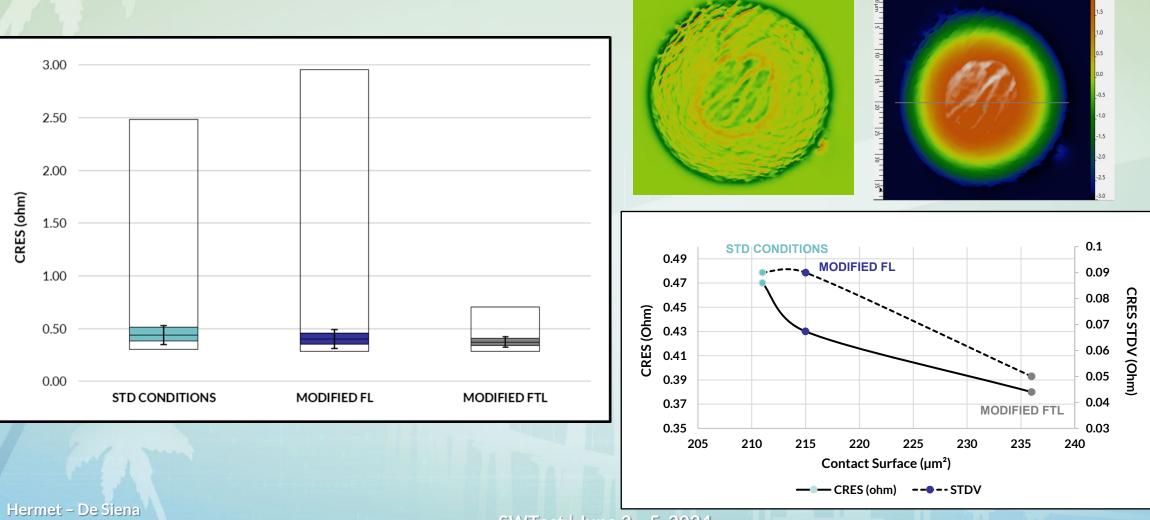
Hermet – De Siena

SWTest | June 3 - 5, 2024

RMS = 250nm

<u>12</u>

Influence of Force Induced by Probe Length CRES Results and Surface Contact Correlation

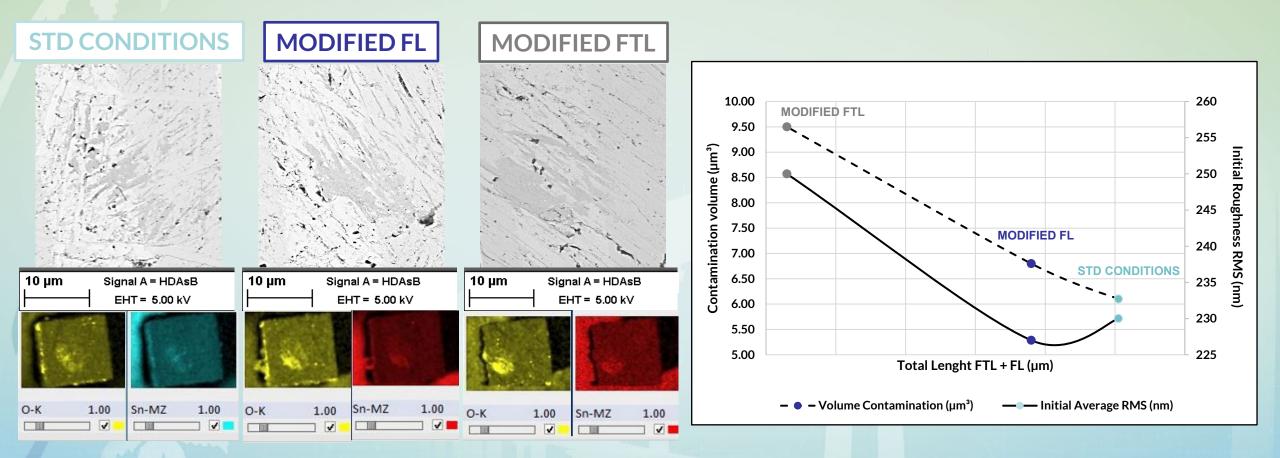


SWTest | June 3 - 5, 2024

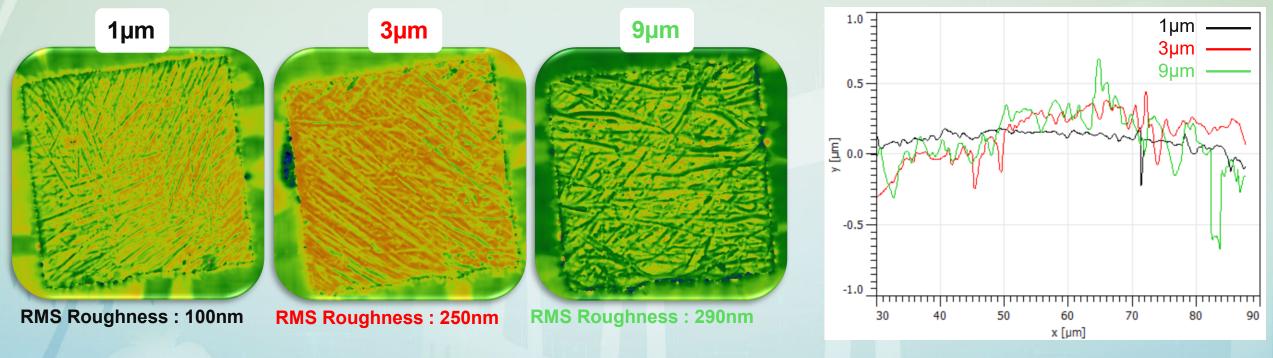
_____5_____10____15____20____25_____30____35____22.2 μn

Influence of Force Induced by Probe Length

• Tip Surface Contamination :



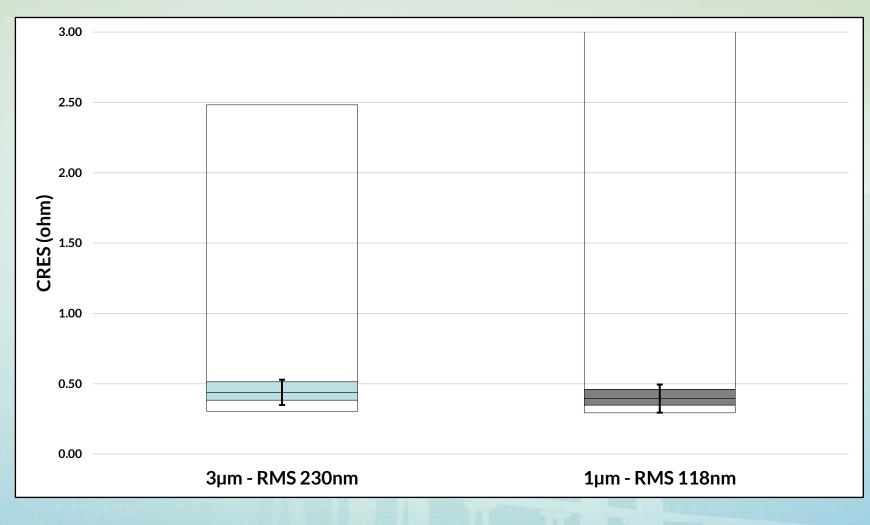
Initial Tip Surface Roughness after Lapping



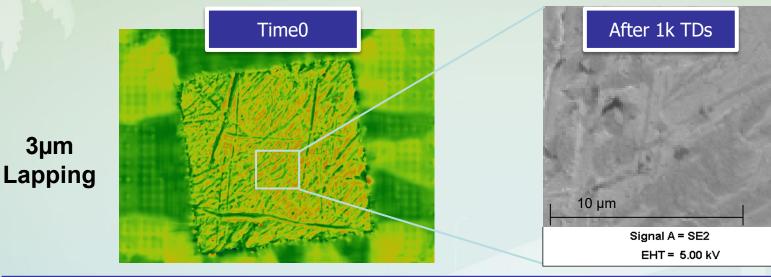
PROFILE

Hermet – De Siena

CRES Results

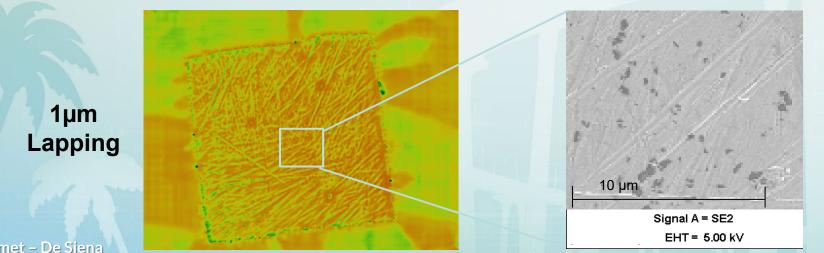


Initial Tip Surface Roughness after Lapping



Surface Roughness RMS = 230 nm

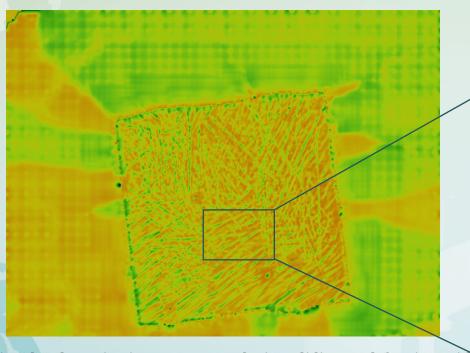
Tin Oxyde Contamination Organic Contamination



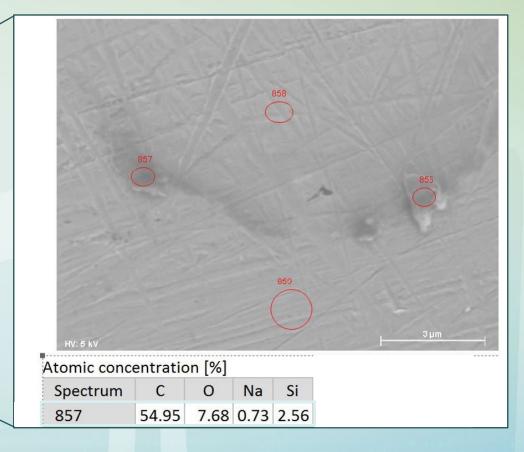
Surface Roughness **RMS = 118 nm**

Organic Contamination Abrasive Contamination

Frictional Polymerization with 1µm Initial Lapping



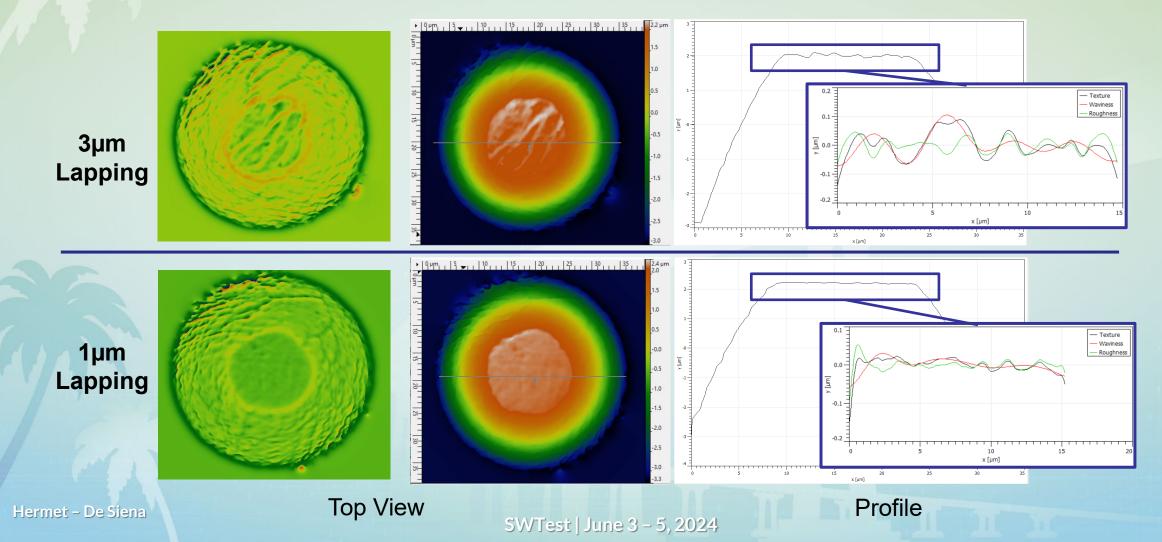
"Frictional polymerization can occur during sliding and fretting with palladium, rhodium and other platinum-group contact metals and alloys due to their catalytic activity. Adsorbed organic air pollutants are converted into complex, solid, insulating contaminants of high molecular weight. Movement enhances this effect, but its role may simply be to dislodge the reaction product, thus producing a continuous conversion to polymers in the area of slide."



Hermet – De Siena

[1] Dr. Morton Antle. The Tribology of Contact Finishes for Electronic Connectors Part I: Mechanisms of Friction and Wear. Plating & Surface Finishing, 75 (10), 46-53 (1988)

Probe Mark Analysis on Bumps



19

Conclusion

• Influence of Current :

Current has few impact on test performance in our test conditions at 30°C in the following range 0.25-250 mA

• Influence of Force Induced by Probe Length :

- Free Tip Length is a contributing factor in reducing CRES and contact variability
- Free Length impacts contact force but not CRES results

• Influence of Initial Tip Surface Conditioning :

 Initial tip roughness influence surface contamination phenomenon for equivalent CRES results

Follow-on Work

Work on tip surface conditioning:

- What is the best surface for our test conditions (Contamination vs CRES)?
- How to maintain this surface clean and conductive (cleaning)
 ?
 - Paper : type nature grain size
 - Cleaning recipe : overdrive speed move frequency
 - New cleaning technology?

Acknowledgement

STMicroelectronics France

- Erziz Salem
- Robert Diperi
- Emeric Pierrard
- Jean-Francois Bosse
- Cedric Hermet

Technoprobe Italy

- Alessio Rigamonti
- Alessandro Mosca
- Andrea Villa
- Elena Brambilla
- Salvatore De Siena



[1] Shin, B.; Kwon, H.-J.; Han, S.-W.; Im, C.M. Fatigue life estimation of vertical probe needle for wafer probing. Int. J. Precis. Eng. Manuf. 2015, 16, 2509–2515.

[2] Le, X.L.; Choa, S.-H.Design of New Au–NiCo MEMS Vertical Probe for Fine-Pitch Wafer-Level Probing. Crystals 2021,11,485. https://doi.org/10.3390/cryst11050485

[3] Chiu, J.-T.; Chang, D.-Y. A new probe design combining finite element method and optimization used for vertical probe card in wafer probing. Precis. Eng. 2009, 33, 395–401.

[4] Oliver Nagler, Tobias Krebs, Michael Heuken. An Improved Model of Electrical Contact Resistance of Pad-Probe Interaction during Wafer Test – September 2019 IEEE Holm Conference on Electrical Contacts. DOI: 10.1109/HOLM.2019.8923892

[5] Jung, H-W., Kim, S-J., Kim, Y-J., Kim, J-Y., Lee, J-Y., Park, J-H., Finite element analysis of vertical micro-probe considering Joule-heating effect, International Journal of Fatigue (2017), doi: http://dx.doi.org/10.1016/j.ijfatigue.2017.02.02

[6] J. Broz and R. M. Rincon, "Probe contact resistance variations during elevated temperature wafer test," International Test Conference 1999. Proceedings (IEEE Cat. No.99CH37034), Atlantic City, NJ, USA, 1999, pp. 396-405, doi: 10.1109/TEST.1999.805761.

[7] David Nečas, Petr Klapetek, Gwyddion: an open-source software for SPM data analysis, Cent. Eur. J. Phys. 10(1) (2012) 181-188

[8] Valery V. Konchits. Polymerization in Friction. Encyclopedia of Tribology pp 2644–2648

[9] January Kister, Steve Hopkins MicroProbe, Inc. Electrical Contact Resistance Electrical Contact Resistance - The Key Parameter in Probe Card The Key Parameter in Probe Card The Key Parameter in Probe Card Performance. IEE SWTest Workshop June 3-6, 2007 San Diego, CA USA San Diego,

